New Jersey Semi-Conductor Products, Inc.

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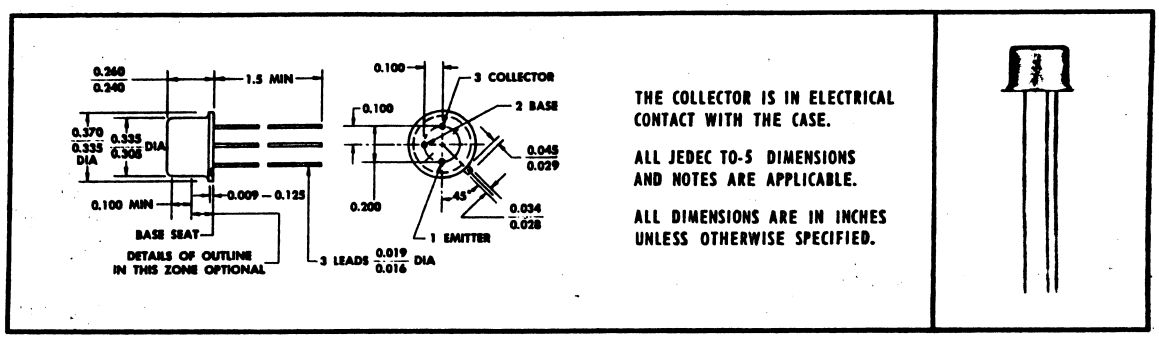
TYPES 2N2192, 2N2192A, 2N2193, 2N2193A, 2N2194, 2N2194A, 2N2243, 2N2243A
N-P-N EPITAXIAL PLANAR SILICON TRANSISTORS

FOR MEDIUM-POWER, HIGH-SPEED SWITCHING AND AMPLIFIER APPLICATIONS

- **High Breakdown Voltage Combined With Very-Low Saturation Voltage**
- **DC Beta — Guaranteed From 100 μa to 1 amp**

***mechanical data**



***absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)**

	2N2192 2N2192A	2N2193 2N2193A	2N2194 2N2194A	2N2243 2N2243A	UNIT
Collector-Base Voltage	60	80	60	120	v
Collector-Emitter Voltage (See Note 1)	40	50	40	80	v
Emitter-Base Voltage	5	8	5	7	v
Collector Current	1	1	1	1	a
Total Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 2)	0.8	0.8	0.8	0.8	w
Total Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	2.8	2.8	2.8	2.8	w
Total Device Dissipation at 100°C Case Temperature	1.6	1.6	1.6	1.6	w
Operating Collector Junction Temperature Range	−65°C to + 200°C				
Storage Temperature Range	−65°C to + 300°C				

NOTES: 1. This value applies when the emitter-base diode is open-circuited.
2. Derate linearly to 200°C free-air temperature at the rate of 4.6 mw/C°.
3. Derate linearly to 200°C case temperature at the rate of 16.0 mw/C°.

*Indicates JEDEC Registered Data.

Quality Semi-Conductors